

TOSHIBA Diode Silicon Epitaxial Planar Type

HN1D03F

Ultra High Speed Switching Application

- Built in anode common and cathode common.

Unit 1

- Low forward voltage Q1, Q2: $V_F(3) = 0.90V$ (typ.)
- Fast reverse recovery time Q1, Q2: $t_{rr} = 1.6ns$ (typ.)
- Small total capacitance Q1, Q2: $C_T = 0.9pF$ (typ.)

Unit 2

- Low forward voltage Q3, Q4: $V_F(3) = 0.92V$ (typ.)
- Fast reverse recovery time Q3, Q4: $t_{rr} = 1.6ns$ (typ.)
- Small total capacitance Q3, Q4: $C_T = 2.2pF$ (typ.)

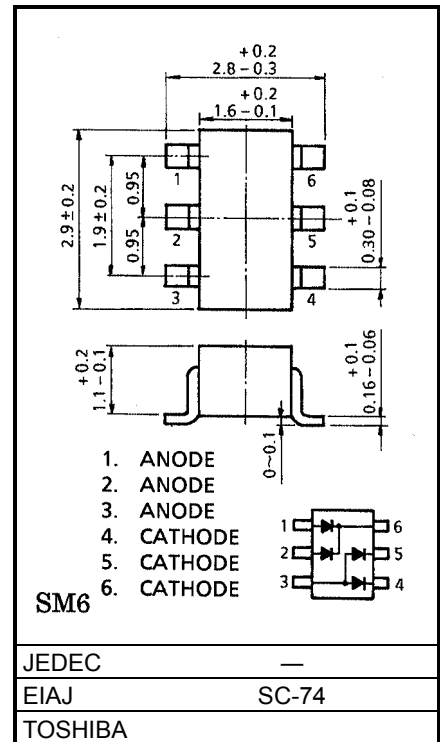
Unit 1, Unit 2 Common Maximum Ratings ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	300 (*)	mA
Average forward current	I_O	100 (*)	mA
Surge current (10ms)	I_{FSM}	2 (*)	A
Power dissipation	P	300	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature range	T_{stg}	-55~125	$^\circ C$

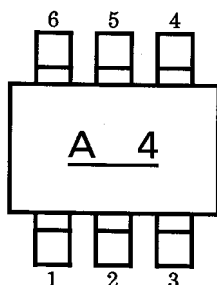
(*) This is the Maximum Ratings of single diode (Q1 or Q2 or Q3 or Q4).

In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.

Unit: mm



Marking



Pin Assignment (Top View)

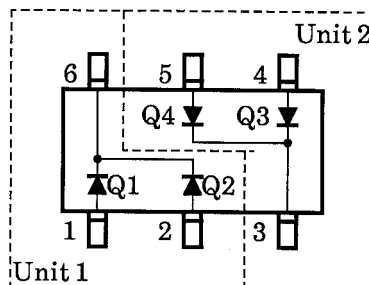
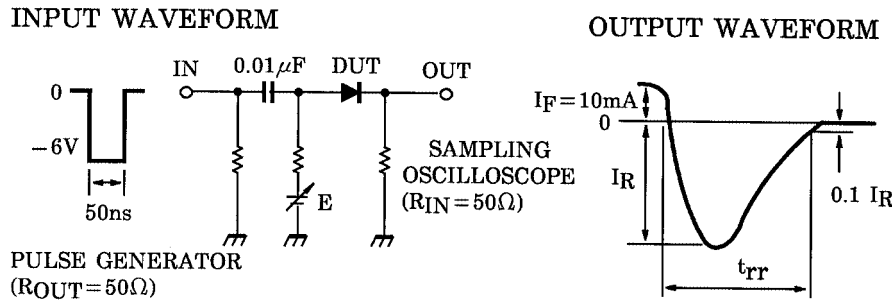


Fig.1 Reverse Recovery Time (t_{rr}) Test Circuit

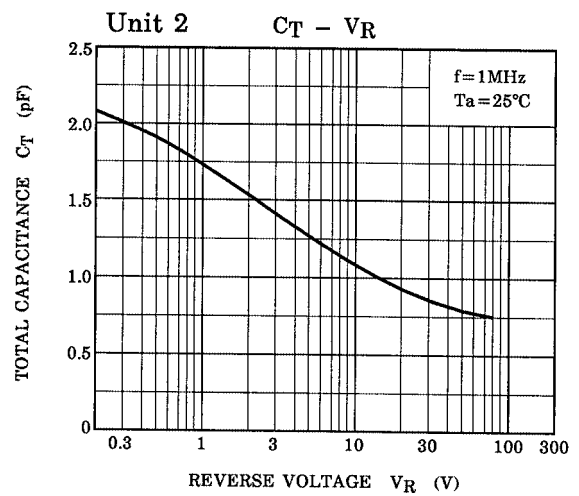
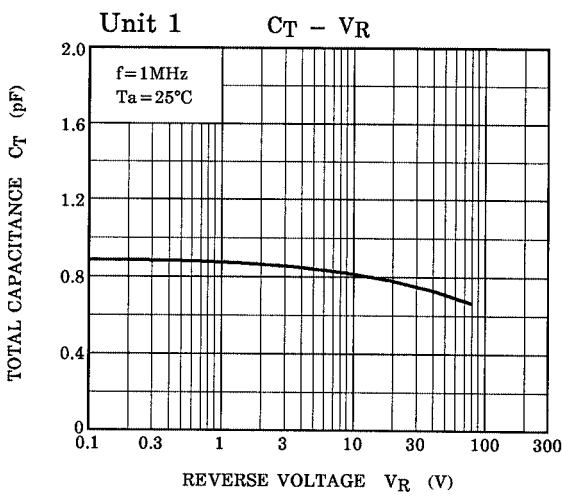
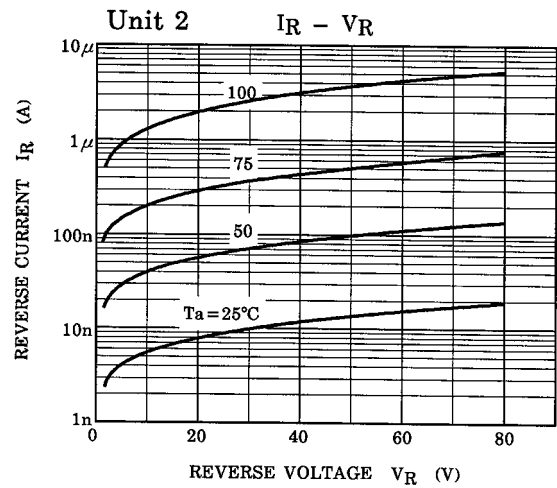
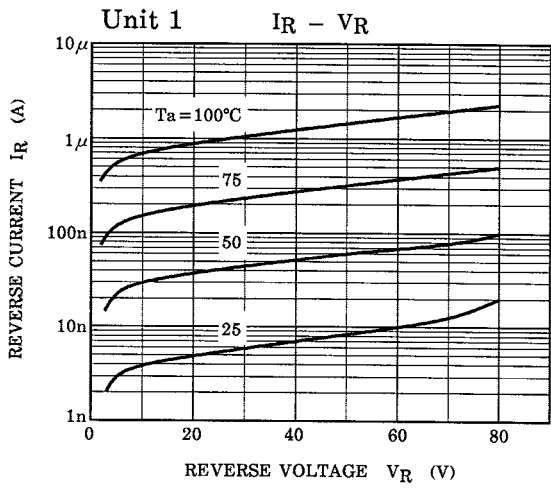
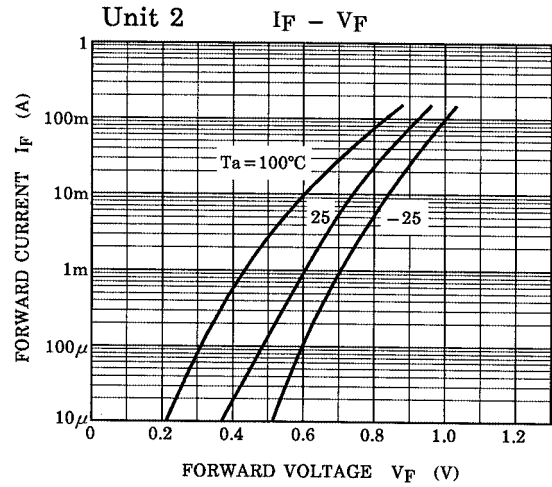
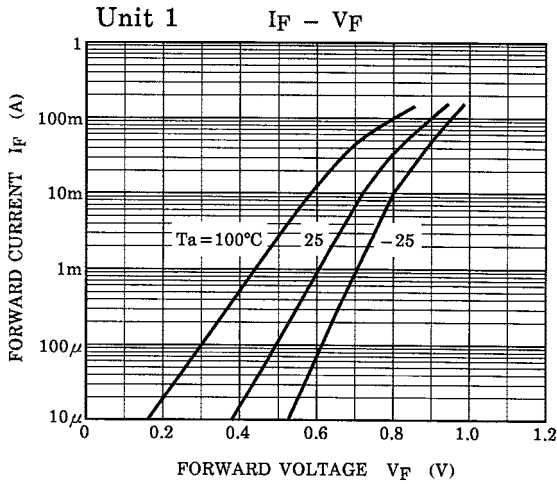


Unit 1 Electrical Characteristics (Q1, Q2, Common) (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V _F (1)	—	I _F = 1mA	—	0.60	—	V
	V _F (2)	—	I _F = 10mA	—	0.72	—	
	V _F (3)	—	I _F = 100mA	—	0.90	1.20	
Reverse current	I _R (1)	—	V _R = 30V	—	—	0.1	µA
	I _R (2)	—	V _R = 80V	—	—	0.5	
Total capacitance	C _T	—	V _R = 0, f = 1MHz	—	0.9	3.0	pF
Reverse recovery time	t _{rr}	—	I _F = 10mA (fig.1)	—	1.6	4.0	ns

Unit 2 Electrical Characteristics (Q3, Q4, Common) (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V _F (1)	—	I _F = 1mA	—	0.61	—	V
	V _F (2)	—	I _F = 10mA	—	0.74	—	
	V _F (3)	—	I _F = 100mA	—	0.92	1.20	
Reverse current	I _R (1)	—	V _R = 30V	—	—	0.1	µA
	I _R (2)	—	V _R = 80V	—	—	0.5	
Total capacitance	C _T	—	V _R = 0, f = 1MHz	—	2.2	4.0	pF
Reverse recovery time	t _{rr}	—	I _F = 10mA (fig.1)	—	1.6	4.0	ns



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